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(54) Title: INITIATION MODULATION FOR PLASMA DEPOSITION

(57) Abstract: Exemplary deposition methods may include forming a plasma of an oxygen-containing precursor within a processing region of a semiconductor processing chamber. The processing region may house a semiconductor substrate on a substrate support. The methods may include, while maintaining the plasma of the oxygen-containing precursor, flowing a silicon-containing precursor into the processing region of the semiconductor processing chamber at a first flow rate. The methods may include ramping the first flow rate of the silicon-containing precursor over a period of time to a second flow rate greater than the first flow rate. The methods may include depositing a silicon-containing material on the semiconductor substrate.

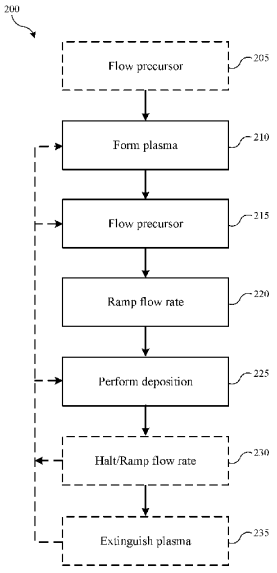

FIG. 2

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